N-Channel Enhancement Silicon MOSFET



3SK248

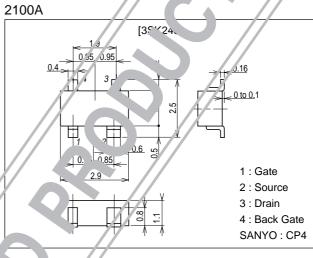
# **Muting/Switching Applications**

#### Features

- · MOSFET with a back gate terminal.
- · Enhancement type.
- · Small ON resistance.
- · Small-sized package permitting 3SK248-applied sets to be made smaller and slimmer.

### Package Dimensions

unit:mm



### **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

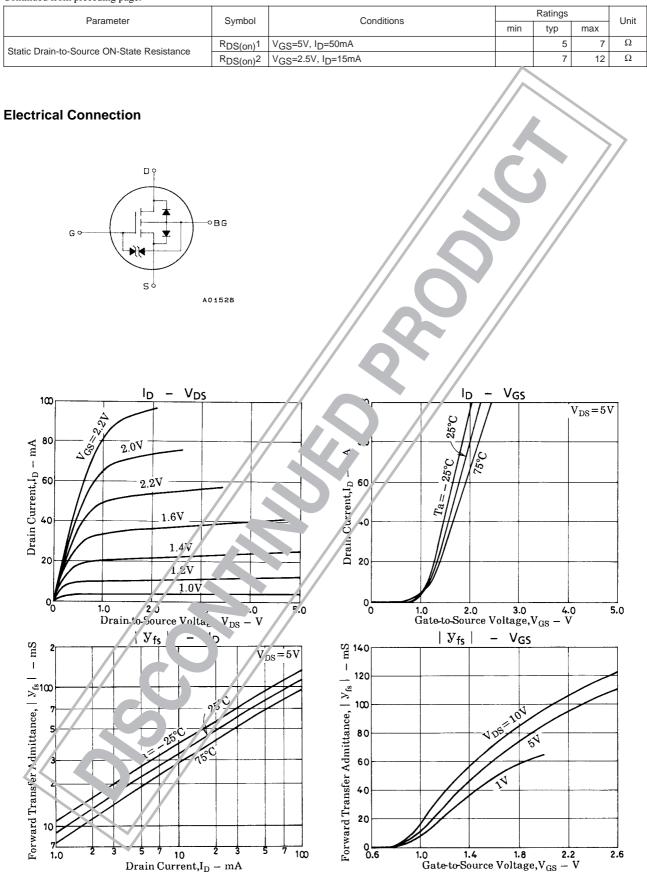
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		10	V
Gate-to-Source Voltage	V <sub>SSS</sub>		±10	V
Drain Current (DC)	1/D		100	mA
Allowable Power Dissipation	PD		200	mW
Channel Temperature	Tch		125	°C
Storage Temperature	Ts*q		-55 to +125	°C

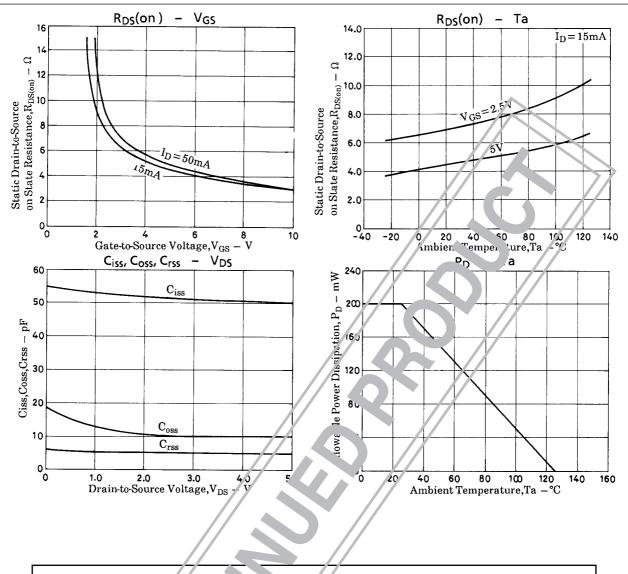
## Electrical Characteristics *a T*a = 25 *C*

Parameter	Symbo.	Conditions	Ratings			Unit	
Farameter			min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	JSS	I <sub>D</sub> -10μA, V <sub>GS</sub> =0V	10			V	
Gate-to-Source Breakdown Valtr ge	VGSS	'G=±10μA, V <sub>DS</sub> =0V	±10			V	
Zero-Gate Voltage Drain Current	DSS	Y <sub>DS</sub> =5V, V <sub>GS</sub> =0V			1	μA	
Gate-to-Source Leakage Crurrent	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V		±0.01	±50	nA	
Cutoff Voltage	VGS(ofi)	V <sub>DS</sub> =5V, I <sub>D</sub> =100μA	0.3		1.5	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =5V, I <sub>D</sub> =50mA, f=1kHz		80		mS	
Input Capacitance	Ciss	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz		50		pF	
Output Capacilar ce	Coss	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz		10		pF	
Reverse Transfer Capabila.	Crss	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz		5		pF	
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